

# 5DS19B

## Switching Diode



### Features

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- High-speed

Item	Characteristics
Wafer size	5inch
Chip size	235*235um

### Maximum Ratings @25degC

Item	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	VRRM	100	V
Continuous Reverse Voltage	VR	100	V
Continuous Forward Current	IF	200	mA
Repetitive Peak Forward Current	IFRM	450	mA
Non-Repetitive Peak Forward Current @t=1us	IFSM	4	A
Non-Repetitive Peak Forward Current @t=1ms		1	A
Non-Repetitive Peak Forward Current @t=1s		0.5	A
Total Power Dissipation	Ptot	500	mW
Storage Temperature	Tstg	-65to+200	degC
Junction Temperature	Tj	200	degC

### Conformance Characteristic @25degC

Symbol	Min	Max	Unit	Test Condition
VF1	-	-	mV	IF=0.2mA
VF2	640	710	mV	IF=5mA
VF3		1010	mV	IF=100mA
VF4		1450	mV	IF=500mA
IR1		23	nA	VR=20V
IR2		45	nA	VR=50V
IR3		500	nA	VR=75V
BV	105		V	IR=10uA
CT		2	pF	VR=0V, f=1MHz
trr		4	nsec	IF=10mA, IR=10mA, irr=1mA

### Note

Equivalent type : BAW62

SheetNo.

Rev.